# 512K x 8 SRAM
## 3.3 VOLT HIGH SPEED SRAM with CENTER POWER PINOUT

### AVAILABLE AS MILITARY SPECIFICATIONS
•MIL-STD-883 for Ceramic
•Extended Temperature Plastic (COTS)

### FEATURES
- Ultra High Speed Asynchronous Operation
- Fully Static, No Clocks
- Multiple center power and ground pins for improved noise immunity
- Easy memory expansion with CE\ and OE\ options
- All inputs and outputs are TTL-compatible
- Single +3.3V Power Supply +/- 0.3V
- Data Retention Functionality Testing
- Cost Efficient Plastic Packaging
- Extended Testing Over -55ºC to +125ºC for plastics

### OPTIONS — MARKING

- Timing

| | |
|---|---|
| 12ns access | -12 |
| 15ns access | -15 |
| 20ns access | -20 |
| 25ns access | -25 |

- Operating Temperature Ranges
  Military (-55ºC to +125ºC) XT
  Industrial (-40ºC to +85ºC) IT

- Package(s)

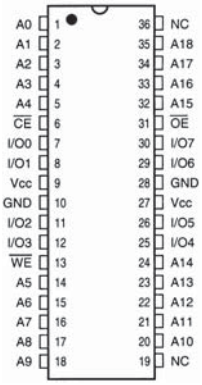
| | | |
|---|---|---|
| Ceramic Flatpack | F | No. 307 |
| Plastic SOJ (400 mils wide) | DJ | |
| Ceramic LCC | EC | No. 210 |

- 2V data retention/low power — L

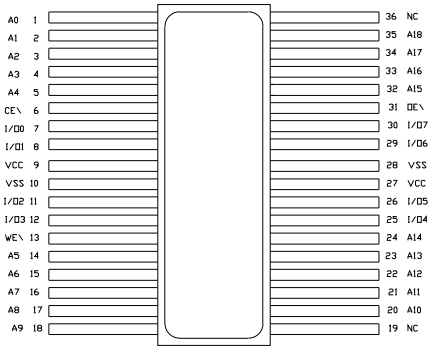
For more products and information please visit our web site at
***www.micross.com***

### PIN ASSIGNMENT
(Top View)

36-Pin PSOJ (DJ)
36-Pin CLCC (EC)




36-Pin Flat Pack (F)




### GENERAL DESCRIPTION

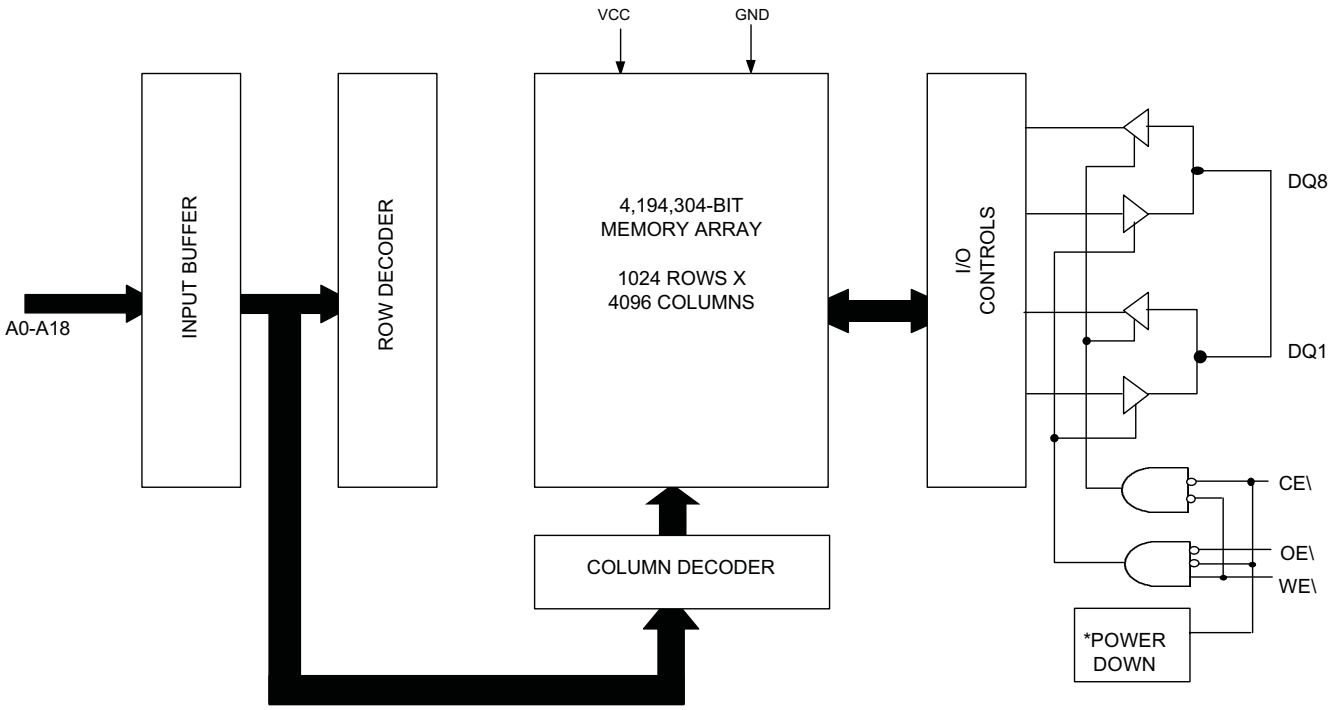
The AS5LC512K8 is a 3.3V high speed SRAM. It offers flexibility in high-speed memory applications, with chip enable (CE\) and output enable (OE\) capabilities. These features can place the outputs in High-Z for additional flexibility in system design.

Writing to these devices is accomplished when write enable (WE\) and CE\ inputs are both LOW. Reading is accomplished when WE\ remains HIGH and CE\ and OE\ go LOW.

As a option, the device can be supplied offering a reduced power standby mode, allowing system designers to meet low standby power requirements. This device operates from a single +3.3V power supply and all inputs and outputs are fully TTL-compatible.

The AS5LC512K8DJ offers the convenience and reliability of the AS5LC512K8 SRAM and has the cost advantage of a plastic encapsulation.

## FUNCTIONAL BLOCK DIAGRAM




**On the low voltage Data Retention option.*

### TRUTH TABLE

| MODE | OE\ | CE\ | WE\ | I/O | POWER |
|---|---|---|---|---|---|
| STANDBY | X | H | X | HIGH-Z | STANDBY |
| READ | L | L | H | Q | ACTIVE |
| NOT SELECTED | H | L | H | HIGH-Z | ACTIVE |
| WRITE | X | L | L | D | ACTIVE |

X = Don't Care

PIN FUNCTIONS

| | |
|---|---|
| A0 - A18 | Address Inputs |
| WE\ | Write Enable |
| CE\ | Chip Enable |
| OE\ | Output Enable |
| $I/O_0$ - $I/O_7$ | Data Inputs/Outputs |
| $V_{CC}$ | Power |
| $V_{SS}$ | Ground |
| NC | No Connection |

## ABSOLUTE MAXIMUM RATINGS*

Voltage on Vcc Supply Relative to Vss
Vcc .....-.5V to 4.6V
Storage Temperature .....-65°C to +150°C
Short Circuit Output Current (per I/O)….....20mA
Voltage on any Pin Relative to Vss.....-.5V to 4.6V
Maximum Junction Temperature**.....+150°C
Power Dissipation .....1W

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

** Junction temperature depends upon package type, cycle time, loading, ambient temperature and airflow, and humidity.

## ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS

($-55^oC \le T_A \le +125^oC$ & $-40^oC \le T_A \le +85^oC$ ; Vcc = 3.3V ±0.3%)

| | | | MAX | | | | | |
|---|---|---|---|---|---|---|---|---|
| DESCRIPTION | CONDITIONS | SYM | -12 | -15 | -20 | -25 | UNITS | NOTES |
| Power Supply Current: Operating | CE\ ≤ $V_{IL}$; Vcc = MAX<br>f = MAX = $1/t_{RC}$<br>Outputs Open | $I_{CCSP}$ | 80 | 70 | 60 | 55 | mA | 3, 2 |
| | "L" Version Only | $I_{CCLP}$ | 60 | 50 | 40 | 35 | mA | |
| Power Supply Current: Standby | CE\ ≥ $V_{IH}$, All other inputs ≤ $V_{IL}$,<br>Vcc = MAX, f = 0,<br>Outputs Open | $I_{SBTSP}$ | 20 | 20 | 20 | 20 | mA | |
| | "L" Version Only | $I_{SBTLP}$ | 15 | 15 | 15 | 15 | mA | |
| | CE\ ≥ Vcc -0.2V; Vcc = MAX<br>$V_{IN}$≤Vss +0.2V or<br>$V_{IN}$≥Vcc -0.2V; f = 0 | $I_{SBCSP}$ | 15 | 15 | 15 | 15 | mA | |
| | "L" Version Only | $I_{SBCLP}$ | 9 | 9 | 9 | 9 | mA | |

| DESCRIPTION | CONDITIONS | SYM | MIN | MAX | UNITS | NOTES |
|---|---|---|---|---|---|---|
| Input High (Logic 1) Voltage | | $V_{IH}$ | 2.2 | Vcc +0.3 | V | 1 |
| Input Low (Logic 0) Voltage | | $V_{IL}$ | -0.3 | 0.8 | V | 1 |
| Input Leakage Current | 0V ≤ $V_{IN}$ ≤ Vcc | $I_{LI}$ | -2 | 2 | µA | |
| Output Leakage Current | Output(s) Disabled<br>0V ≤ $V_{OUT}$ ≤ Vcc | $I_{LO}$ | -2 | 2 | µA | |
| Output High Voltage | $I_{OH}$ = -4.0 mA | $V_{OH}$ | 2.4 | --- | V | 1 |
| Output Low Voltage | $I_{OL}$ = 8 mA | $V_{OL}$ | --- | 0.5 | V | 1 |

## CAPACITANCE

| PARAMETER | CONDITIONS | SYMBOL | MAX | UNITS | NOTES |
|---|---|---|---|---|---|
| Input Capacitance | $T_A$ = 25°C, f = 1MHz<br>$V_{IN}$ = 0 | $C_I$ | 9 | pF | 4 |
| Output Capactiance | | Co | 6 | pF | 4 |

## ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(-55°C ≤ $T_A$ ≤ +125°C or -40°C to +85°C; Vcc = 3.3V ±0.3%)

| DESCRIPTION | SYM | -12 | | -15 | | -20 | | -25 | | UNITS | NOTES |
|---|---|---|---|---|---|---|---|---|---|---|---|
| | | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | | |
| **READ CYCLE** | | | | | | | | | | | |
| Read Cycle Time | $t_{RC}$ | 12 | | 15 | | 20 | | 25 | | ns | |
| Address Access Time | $t_{AA}$ | | 12 | | 15 | | 20 | | 25 | ns | |
| Chip Enable Access Time | $t_{ACE}$ | | 12 | | 15 | | 20 | | 25 | ns | |
| Output Hold From Address Change | $t_{OH}$ | 2 | | 2 | | 2 | | 2 | | ns | |
| Chip Enable to Output in Low-Z | $t_{LZCE}$ | 2 | | 2 | | 2 | | 2 | | ns | 4, 6, 7 |
| Chip Disable to Output in High-Z | $t_{HZCE}$ | | 6 | | 7 | | 8 | | 9 | ns | 4, 6, 7 |
| Output Enable Acess Time | $t_{AOE}$ | | 6 | | 7 | | 8 | | 9 | ns | |
| Output Enable to Output in Low-Z | $t_{LZOE}$ | 0 | | 0 | | 0 | | 0 | | ns | 4, 6, 7 |
| Output Disable to Output in High-Z | $t_{HZOE}$ | | 6 | | 7 | | 8 | | 9 | ns | 4, 6, 7 |
| **WRITE CYCLE** | | | | | | | | | | | |
| WRITE Cycle Time | $t_{WC}$ | 12 | | 15 | | 20 | | 25 | | ns | |
| Chip Enable to End of Write | $t_{CW}$ | 8 | | 10 | | 12 | | 13 | | ns | |
| Address Valid to End of Write | $t_{AW}$ | 8 | | 10 | | 12 | | 13 | | ns | |
| Address Setup Time | $t_{AS}$ | 0 | | 0 | | 0 | | 0 | | ns | |
| Address Hold From End of Write | $t_{AH}$ | 0 | | 0 | | 0 | | 0 | | ns | |
| WRITE Pulse Width | $t_{WP}$ | 10 | | 12 | | 15 | | 15 | | ns | |
| Data Setup Time | $t_{DS}$ | 6 | | 7 | | 8 | | 8 | | ns | |
| Data Hold Time | $t_{DH}$ | 1 | | 1 | | 1 | | 1 | | ns | |
| Write Disable to Output in Low-Z | $t_{LZWE}$ | 2 | | 2 | | 2 | | 2 | | ns | 4, 6, 7 |
| Write Enable to Output in High-Z | $t_{HZWE}$ | 5 | | 6 | | 7 | | 7 | | ns | 4, 6, 7 |

## AC TEST CONDITIONS

| | |
|---|---|
| Input pulse levels | Vss to 3.0V |
| Input rise and fall times | 3ns |
| Input timing reference levels | 1.5V |
| Output reference levels | 1.5V |
| Output load | See Figures 1 and 2 |

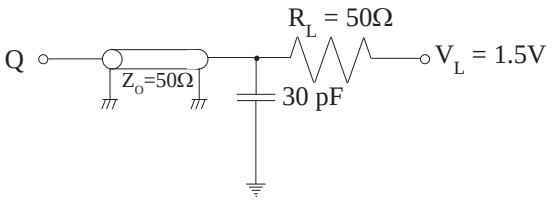



**Fig. 1 Output Load Equivalent**

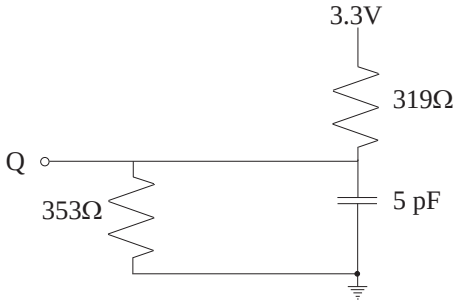



**Fig. 2 Output Load Equivalent**

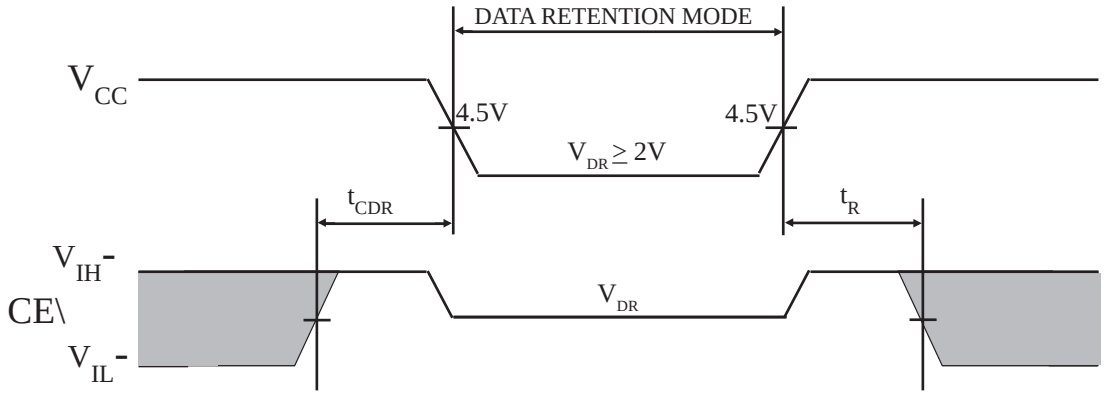
## NOTES

1. All voltages referenced to $V_{SS}$ (GND).
2. $I_{CC}$ limit shown is for absolute worst case switching of ADDR, ADDR\, ADDR, etc.
3. $I_{CC}$ is dependent on output loading and cycle rates.
4. This parameter is guaranteed but not tested.
5. Test conditions as specified with the output loading as shown in Fig. 1 unless otherwise noted.
6. ᵗLZCE, ᵗLZWE, ᵗLZOE, ᵗHZCE, ᵗHZOE and ᵗHZWE are specified with CL = 5pF as in Fig. 2. Transition is measured ±200mV from steady state voltage.
7. At any given temperature and voltage condition, ᵗHZCE is less than ᵗLZCE, and ᵗHZWE is less than ᵗLZWE.
8. WE\ is HIGH for READ cycle.
9. Device is continuously selected. Chip enables and output enables are held in their active state.
10. Address valid prior to, or coincident with, latest occurring chip enable.
11. ᵗRC = Read Cycle Time.
12. Chip enable and write enable can initiate and terminate a WRITE cycle.
13. Output enable (OE\) is inactive (HIGH).
14. Output enable (OE\) is active (LOW).
15. ASI does not warrant functionality nor reliability of any product in which the junction temperature exceeds 150°C. Care should be taken to limit power to acceptable levels.

## DATA RETENTION ELECTRICAL CHARACTERISTICS (L Version Only)

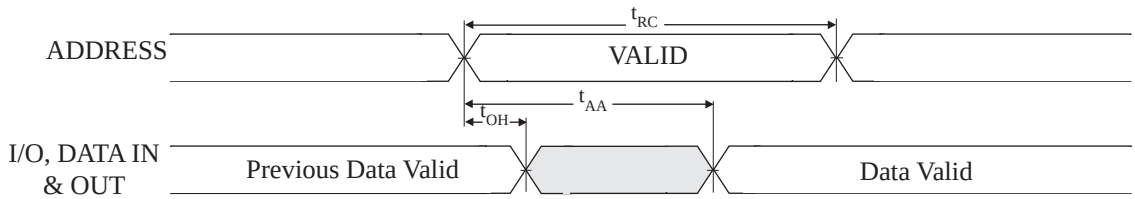
| DESCRIPTION | CONDITIONS | SYM | MIN | MAX | UNITS | NOTES |
|---|---|---|---|---|---|---|
| Vcc for Retention Data | CE\ > $V_{CC}$ -0.2V<br>$V_{IN}$ > $V_{CC}$ -0.2 or 0.2V | $V_{DR}$ | 2 | | V | |
| Data Retention Current | Vcc = 2.0V | $I_{CCDR}$ | | 6.5 | mA | |
| Chip Deselect to Data | | $t_{CDR}$ | 0 | | ns | 4 |
| Operation Recovery Time | | $t_R$ | 20 | | ms | 4, 11 |

## LOW $V_{CC}$ DATA RETENTION WAVEFORM



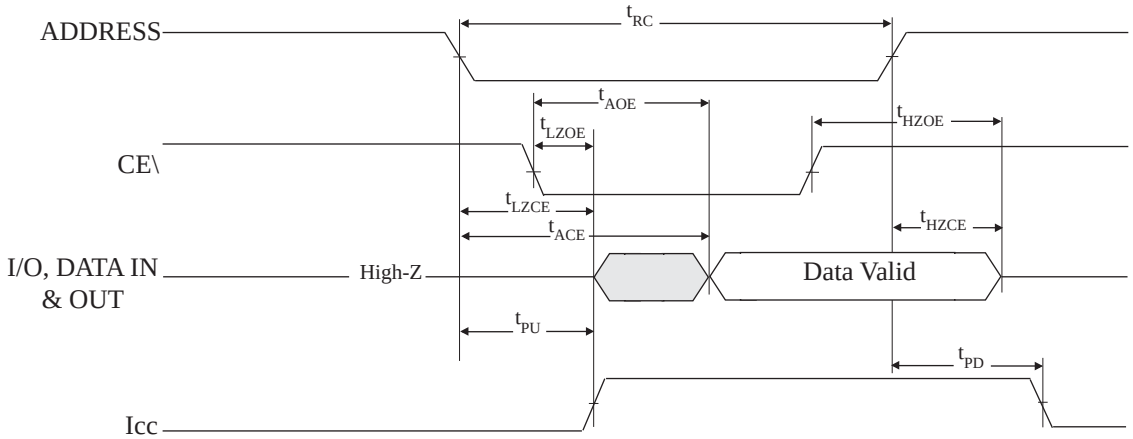

## READ CYCLE NO. 1[1, 2]

(Address Controlled, CE\ = OE\ = $V_{IL}$, WE\ = $V_{IH}$)




## READ CYCLE NO. 2

(WE\ = $V_{IH}$)



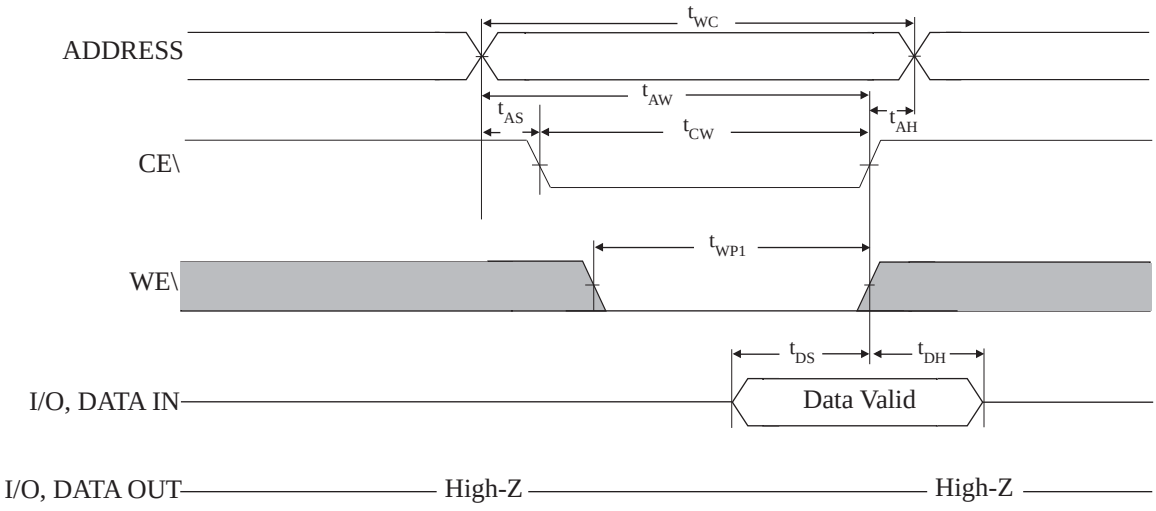

**NOTES:**

1. WE\ is HIGH for READ cycle.
2. Device is continuously selected. Chip enables and output enables are held in their active state.

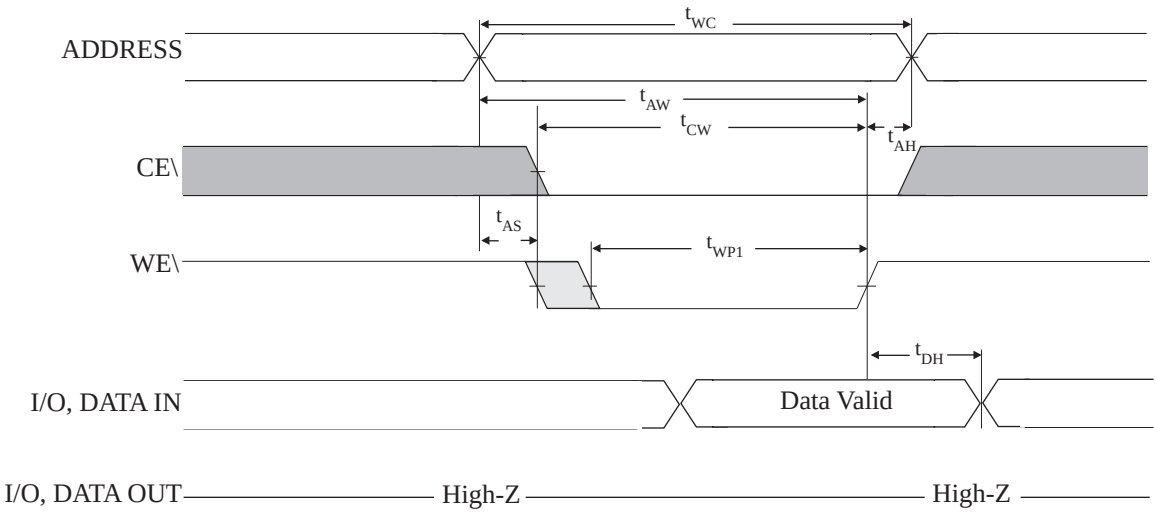
**Don't Care**

**Undefined**

## WRITE CYCLE NO. 1[1]
(CE Controlled)

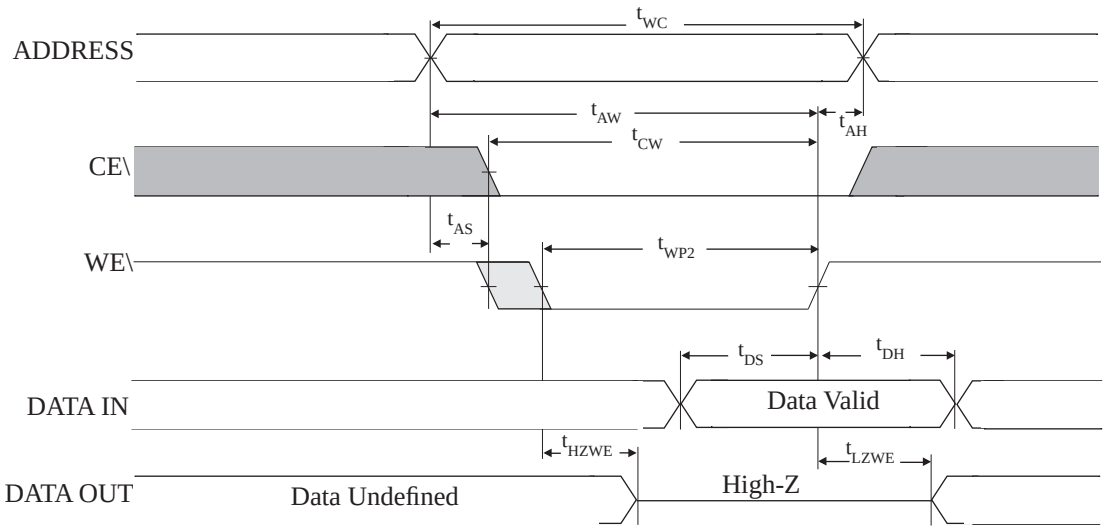



## WRITE CYCLE NO. 2[1, 2]
(Write Enabled Controlled)




**NOTES:**
1. Chip enable and write enable can initiate and terminate a WRITE cycle.
2. Output enable (OE\) is inactive (HIGH).

## WRITE CYCLE NO. 3[1, 2, 3]
(WE Controlled)

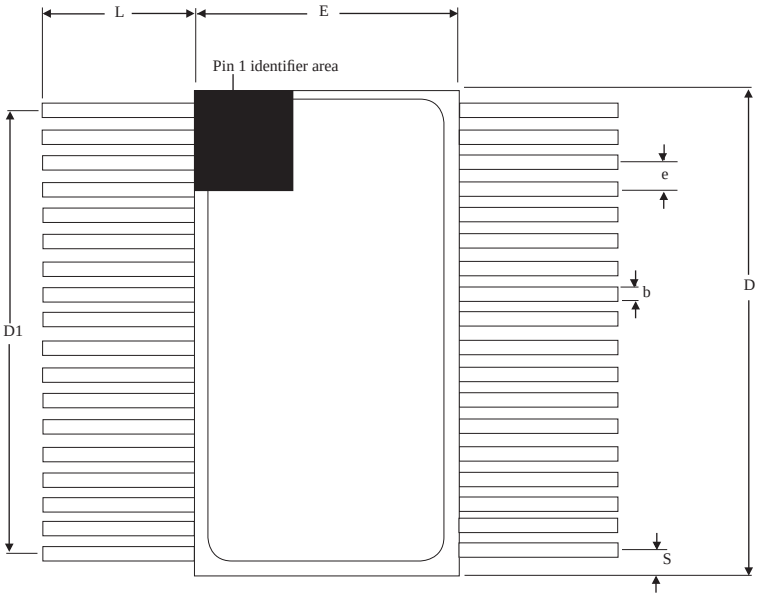



**NOTES:**

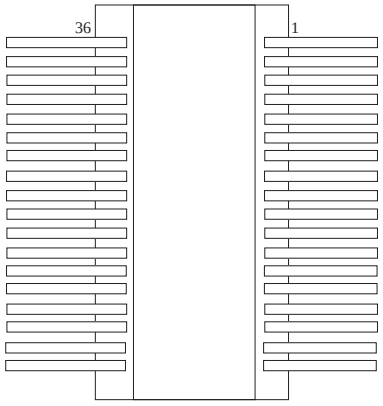
1. At any given temperature and voltage condition, $t_{HZCE}$ is less than $t_{LZCE}$, and $t_{HZWE}$ is less than $t_{LZWE}$.
2. Chip enable and write enable can initiate and terminate a WRITE cycle.
3. Output enable (OE\) is active (LOW).

# MECHANICAL DEFINITIONS*

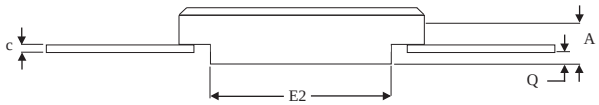
## Micross Case #307 (Package Designator F)




**Top View**




**Bottom View**

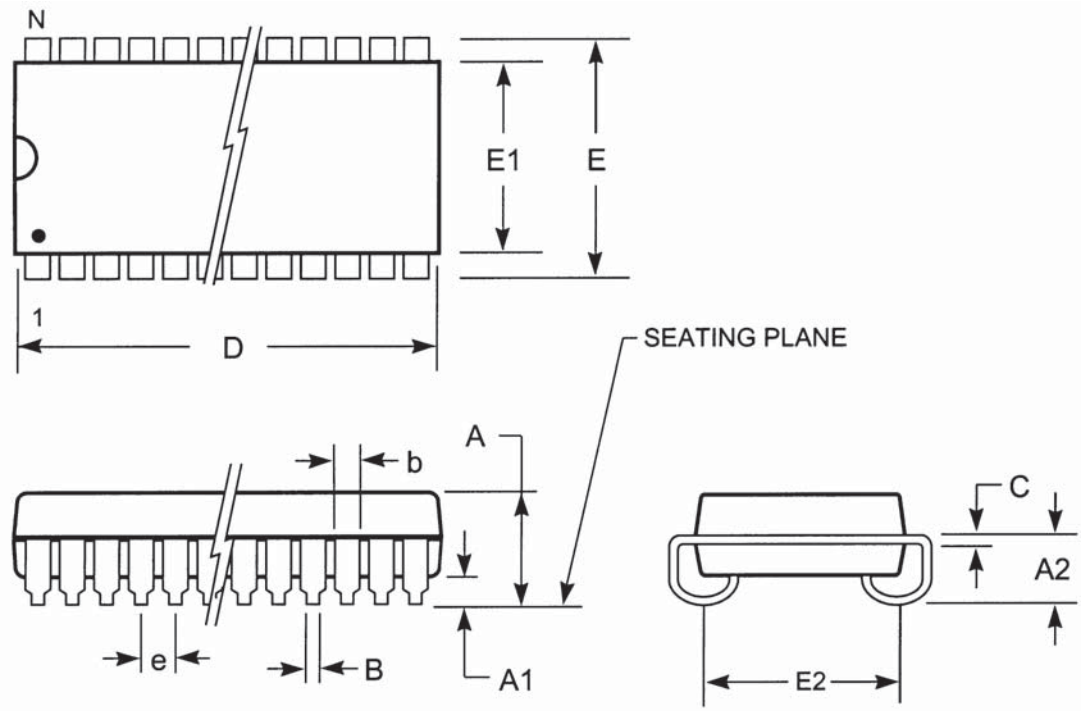



| SYMBOL | MICROSS SPECIFICATIONS | |
|---|---|---|
| | MIN | MAX |
| A | 0.096 | 0.125 |
| b | 0.015 | 0.022 |
| c | 0.003 | 0.009 |
| D | 0.910 | 0.930 |
| D1 | 0.840 | 0.860 |
| E | 0.505 | 0.515 |
| E2 | 0.385 | 0.397 |
| e | 0.050 BSC | |
| L | 0.250 | 0.370 |
| Q | 0.020 | 0.045 |

***All measurements are in inches.***

# MECHANICAL DEFINITIONS*

## Package Designator DJ

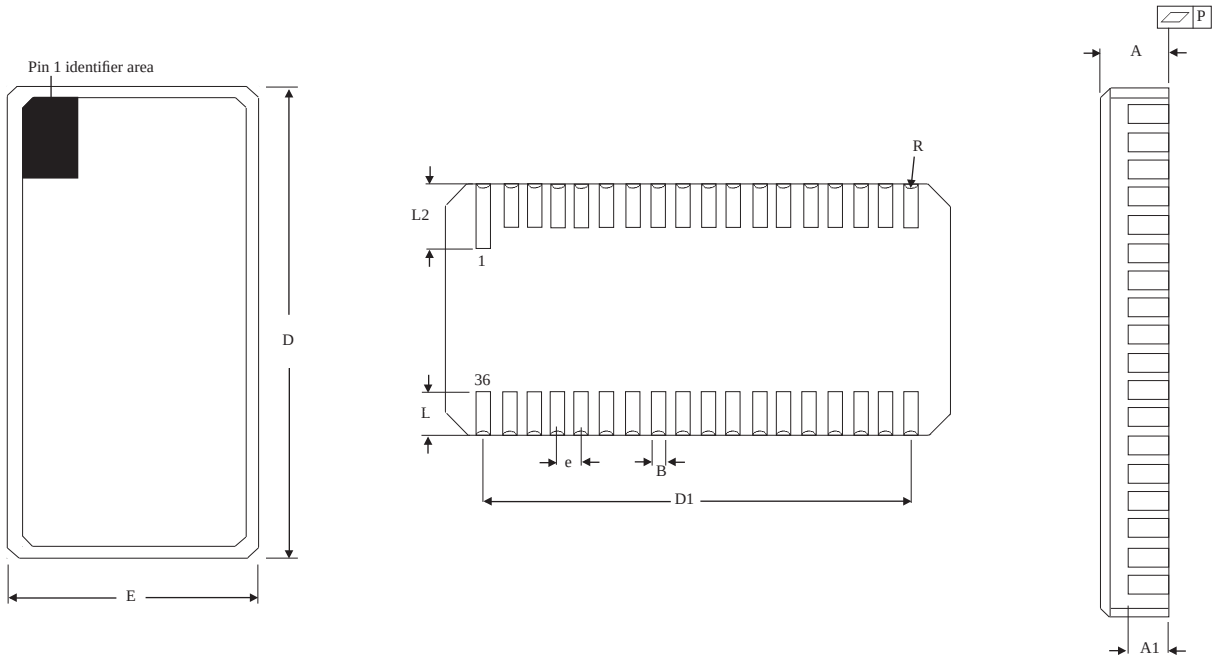



| SYMBOL | MICROSS SPECIFICATIONS | |
|---|---|---|
| | MIN | MAX |
| A | 0.128 | 0.148 |
| A1 | 0.025 | --- |
| A2 | 0.082 | --- |
| B | 0.015 | 0.020 |
| b | 0.026 | 0.032 |
| C | 0.007 | 0.013 |
| D | 0.920 | 0.930 |
| E | 0.435 | 0.445 |
| E1 | 0.395 | 0.405 |
| E2 | 0.370 BSC | |
| e | 0.050 BSC | |

***All measurements are in inches.***

# MECHANICAL DEFINITIONS*

## Micross Case #210 (Package Designator EC)




| SYMBOL | MICROSS SPECIFICATIONS | |
|---|---|---|
| | MIN | MAX |
| A | 0.080 | 0.100 |
| A1 | 0.054 | 0.066 |
| B | 0.022 | 0.028 |
| D | 0.910 | 0.930 |
| D1 | 0.840 | 0.860 |
| E | 0.445 | 0.460 |
| e | 0.050 BSC | |
| L | 0.100 TYP | |
| L2 | 0.115 | 0.135 |
| P | --- | 0.006 |
| R | 0.009 TYP | |

***All measurements are in inches.***

# ORDERING INFORMATION

**EXAMPLE:** AS5LC512K8F-12L/XT

| Device Number | Package Type | Speed ns | Options** | Process |
|---|---|---|---|---|
| AS5LC512K8 | F | -12 | L | /* |
| AS5LC512K8 | F | -15 | L | /* |
| AS5LC512K8 | F | -20 | L | /* |
| AS5LC512K8 | F | -25 | L | /* |

**EXAMPLE:** AS5LC512K8DJ-20L/883C

| Device Number | Package Type | Speed ns | Options** | Process |
|---|---|---|---|---|
| AS5LC512K8 | DJ | -12 | L | /* |
| AS5LC512K8 | DJ | -15 | L | /* |
| AS5LC512K8 | DJ | -20 | L | /* |
| AS5LC512K8 | DJ | -25 | L | /* |

**EXAMPLE:** AS5LC512K8EC-15L/IT

| Device Number | Package Type | Speed ns | Options** | Process |
|---|---|---|---|---|
| AS5LC512K8 | EC | -12 | L | /* |
| AS5LC512K8 | EC | -15 | L | /* |
| AS5LC512K8 | EC | -20 | L | /* |
| AS5LC512K8 | EC | -25 | L | /* |

## *AVAILABLE PROCESSES

IT = Industrial Temperature Range -40°C to +85°C
XT = Extended Temperature Range -55°C to +125°C
883C = Full Military Processing[1] -55°C to +125°C

## **OPTIONS DEFINITIONS

L = 2V Data Retention / Low Power

**NOTES:** 1. 883C process available with ceramic packaging only.

**DOCUMENT TITLE**

512K x 8 SRAM 3.3 VOLT HIGH SPEED SRAM with CENTER POWER PINOUT

| Rev # | History | Release Date | Status |
|---|---|---|---|
| 2.1 | Pg 1: Changed 0.3% to 0.3V | August 2009 | Release |
| 2.2 | Updated Micross Information | January 2010 | Release |